



# BUK753R4-30B

## N-channel TrenchMOS standard level FET

Rev. 2 — 21 April 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	<a href="#">11</a> -	-	75	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	255	W

#### Static characteristics

$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	2.9	3.4	mΩ
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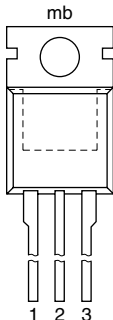
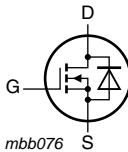
**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ }^\circ\text{C}$ ; unclamped	-	-	1.3	J
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 24\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 14</a>	-	23	-	nC

[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78A (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK753R4-30B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	30	V	
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	30	V	
$V_{GS}$	gate-source voltage		-20	20	V	
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	<a href="#">[1][2]</a>	-	198	A
			<a href="#">[3]</a>	-	75	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	<a href="#">[3]</a>	-	75	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ see <a href="#">Figure 3</a>	-	794	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	255	W	
$T_{stg}$	storage temperature		-55	175	°C	
$T_j$	junction temperature		-55	175	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	<a href="#">[1][2]</a>	-	198	A
			<a href="#">[3]</a>	-	75	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}$	-	794	A	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped	-	1.3	J	
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		<a href="#">[4][5]</a>	-	J	

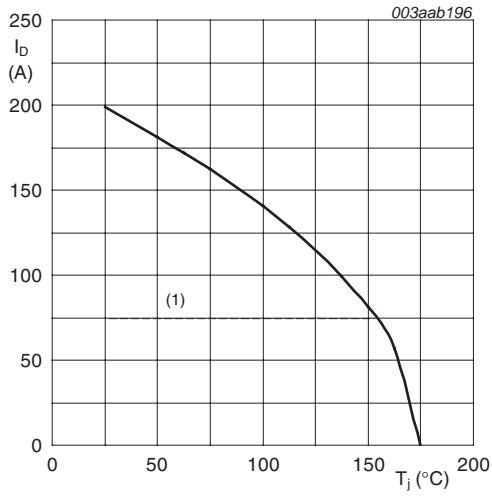
[1] Current is limited by power dissipation chip rating.

[2] Refer to document 9397 750 12572 for further information.

[3] Continuous current is limited by package.

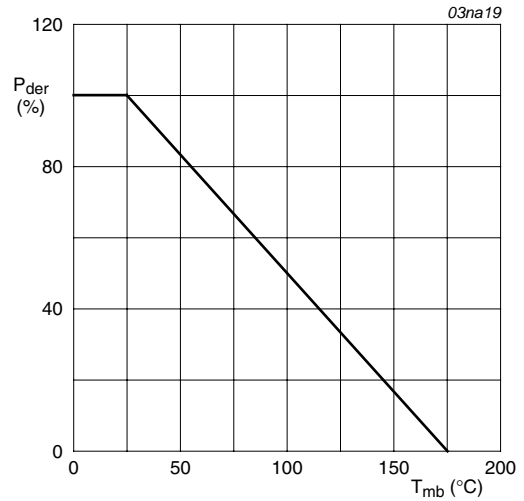
[4] Max value not quoted; Single-shot avalanche rating limited by  $T_j(max)$  of 175 °C.

[5] Repetitive avalanche rating limited by an average  $T_j$  of 170 °C; Refer to application note AN10273 for further information.



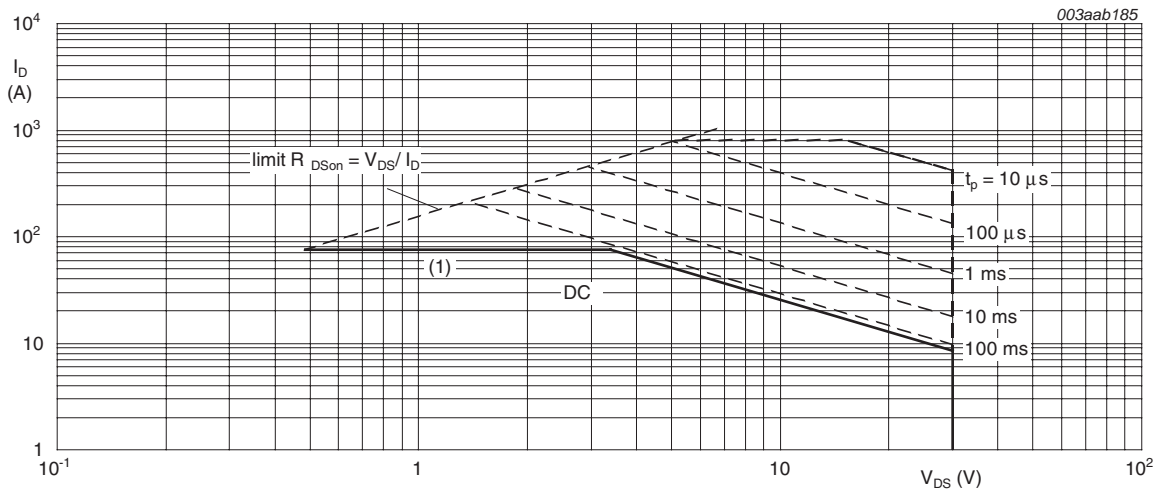
$V_{GS} \geq 5 V$   
 (1) Capped at 75 A due to package.

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



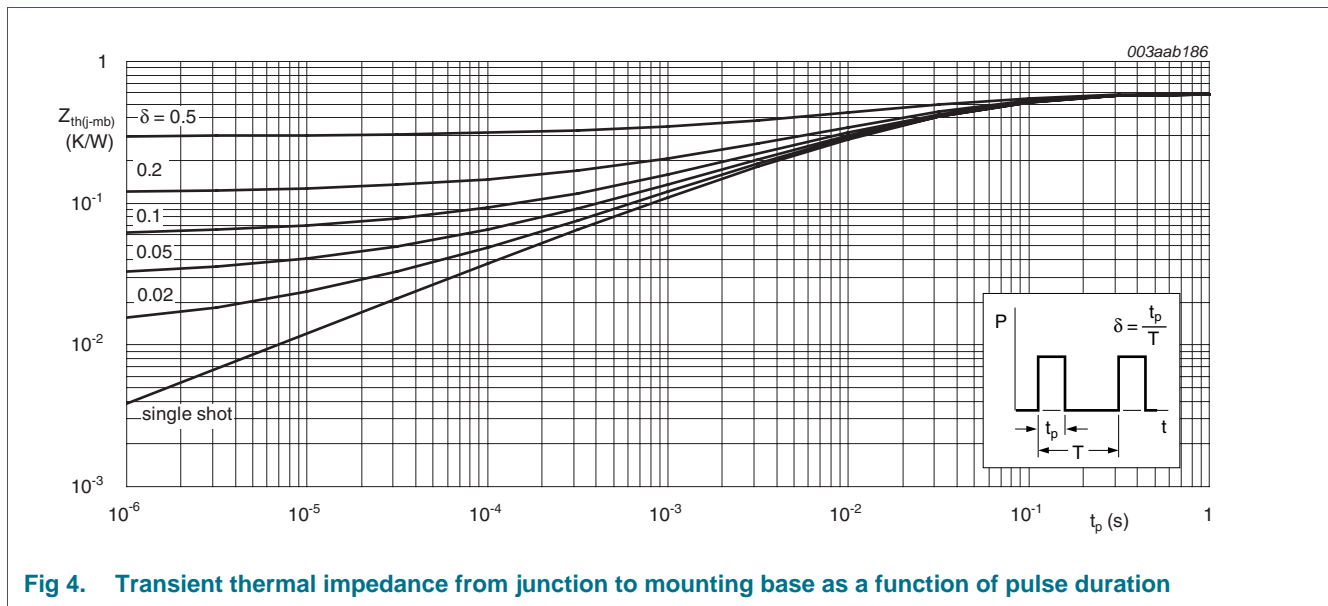
$T_{mb} = 25^\circ C; I_{DM}$  is single pulse  
 (1) Capped at 75 A due to package.

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

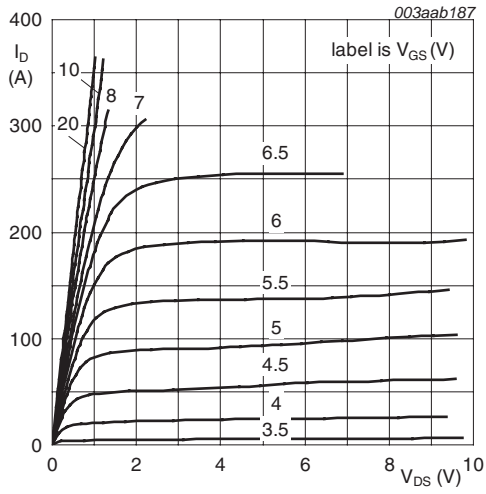
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.59	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



## 6. Characteristics

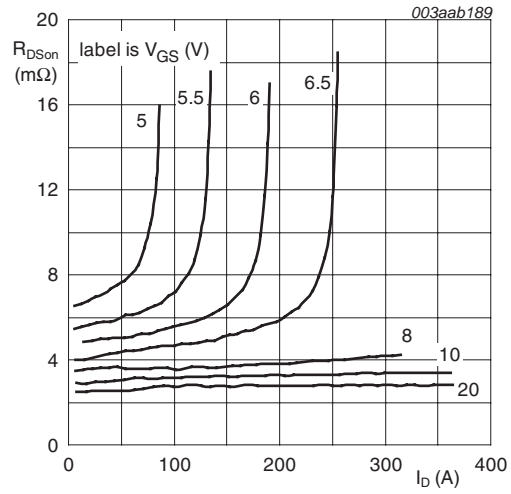
**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	2	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.05	10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	2.9	3.4	m $\Omega$
		$V_{GS} = 10 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	-	6.5	m $\Omega$
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	$\mu A$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a>	-	75	-	nC
$Q_{GS}$	gate-source charge		-	19	-	nC
$Q_{GD}$	gate-drain charge		-	23	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 15</a>	-	3713	4951	pF
$C_{oss}$	output capacitance		-	1249	1499	pF
$C_{rss}$	reverse transfer capacitance		-	460	630	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 V; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 V$ ; $R_{G(ext)} = 10 \text{ } \Omega$	-	32	-	ns
$t_r$	rise time		-	64	-	ns
$t_{d(off)}$	turn-off delay time		-	89	-	ns
$t_f$	fall time		-	71	-	ns
$L_D$	internal drain inductance	from contact screw on mounting base to centre of die	-	3.5	-	nH
		from drain lead 6 mm from package to centre of die	-	4.5	-	nH
$L_S$	internal source inductance	from source lead to source bond pad	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 16</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 A; dI_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 V$ ; $V_{DS} = 30 V$	-	70	-	ns
$Q_r$	recovered charge		-	58	-	nC



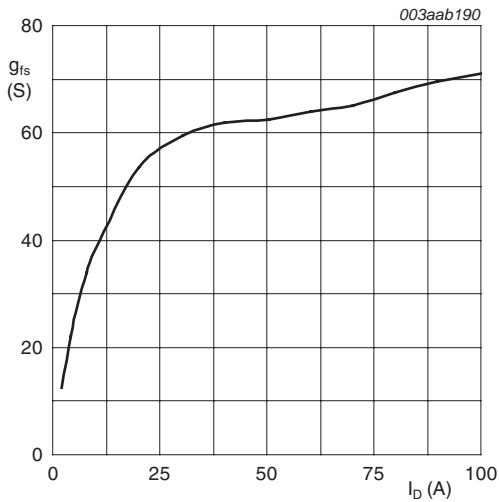
$T_j = 25\text{ }^\circ\text{C}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



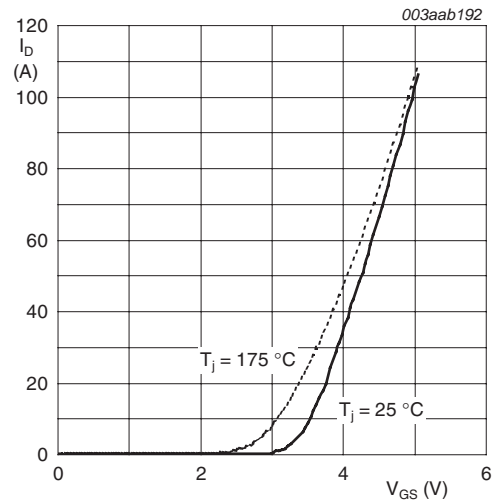
$T_j = 25\text{ }^\circ\text{C}$

**Fig 6. Drain-source on-state resistance as a function of drain current; typical values**



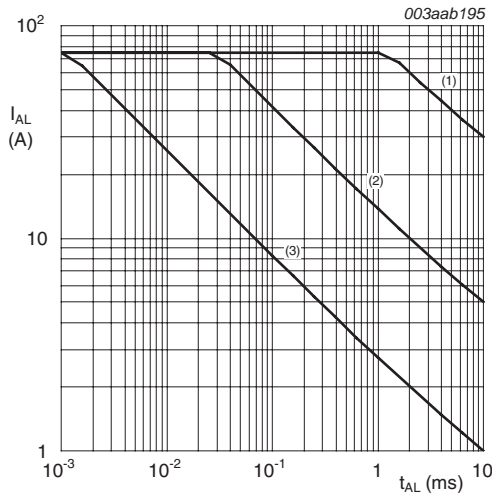
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 25\text{ V}$

**Fig 7. Forward transconductance as a function of drain current; typical values**

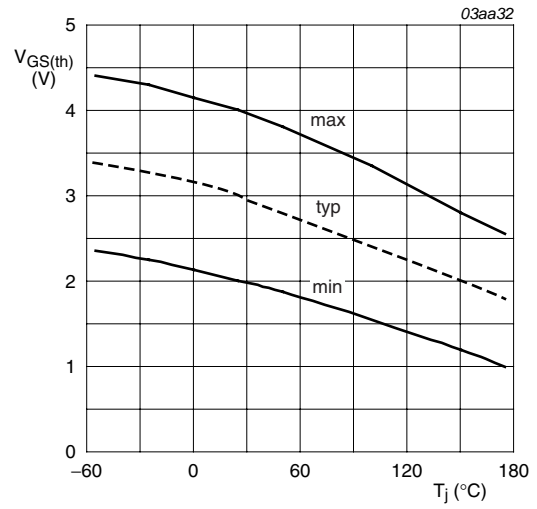


$V_{DS} = 25\text{ V}$

**Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values**

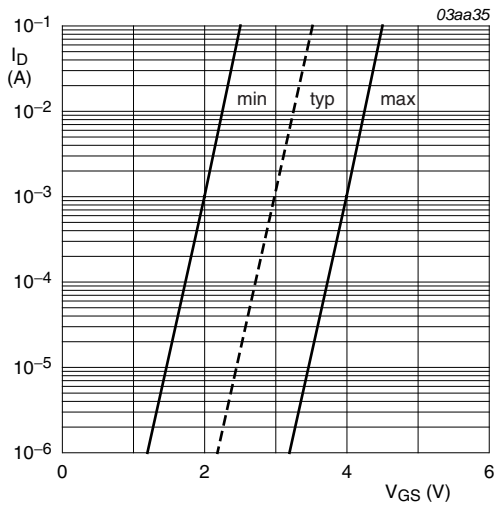


**Fig 9. Single shot and repetitive avalanche rating; avalanche current as a function of avalanche time**



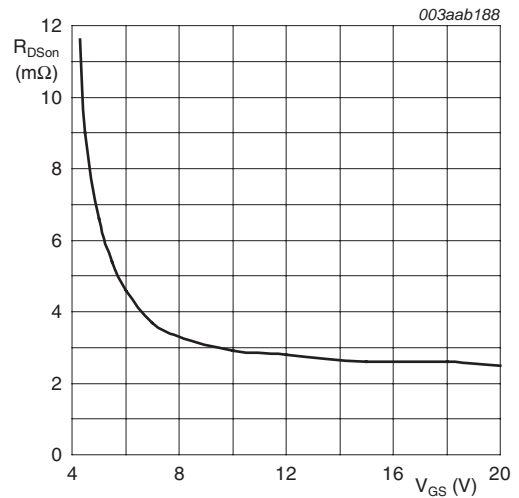
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

**Fig 10. Gate-source threshold voltage as a function of junction temperature**



$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{V}$$

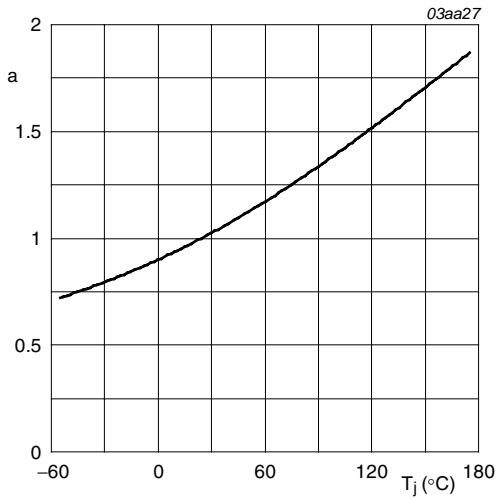
**Fig 11. Sub-threshold drain current as a function of gate-source voltage**



$$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$$

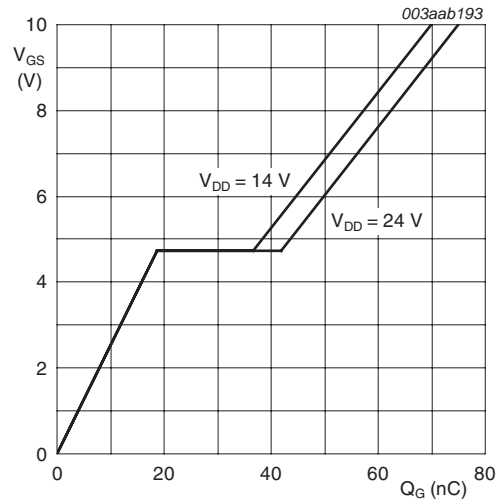
**Fig 12. Drain-source on-state resistance as a function of gate-source voltage; typical values**





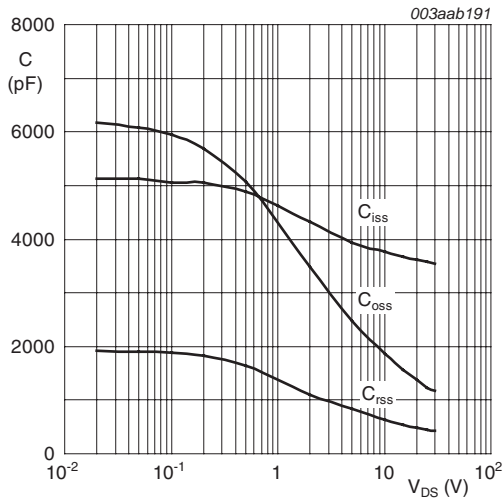
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature**



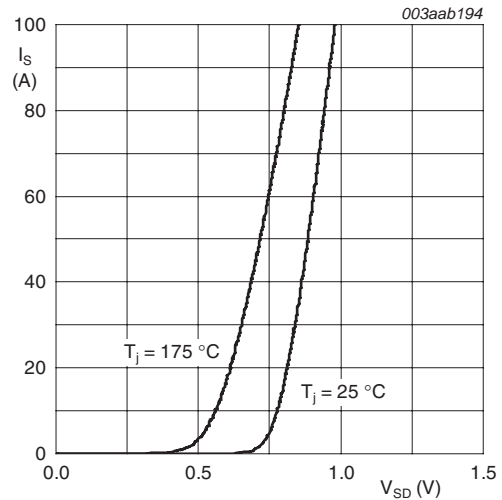
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values**



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

**Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.**



$V_{GS} = 0\text{V}$

**Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

**7. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A

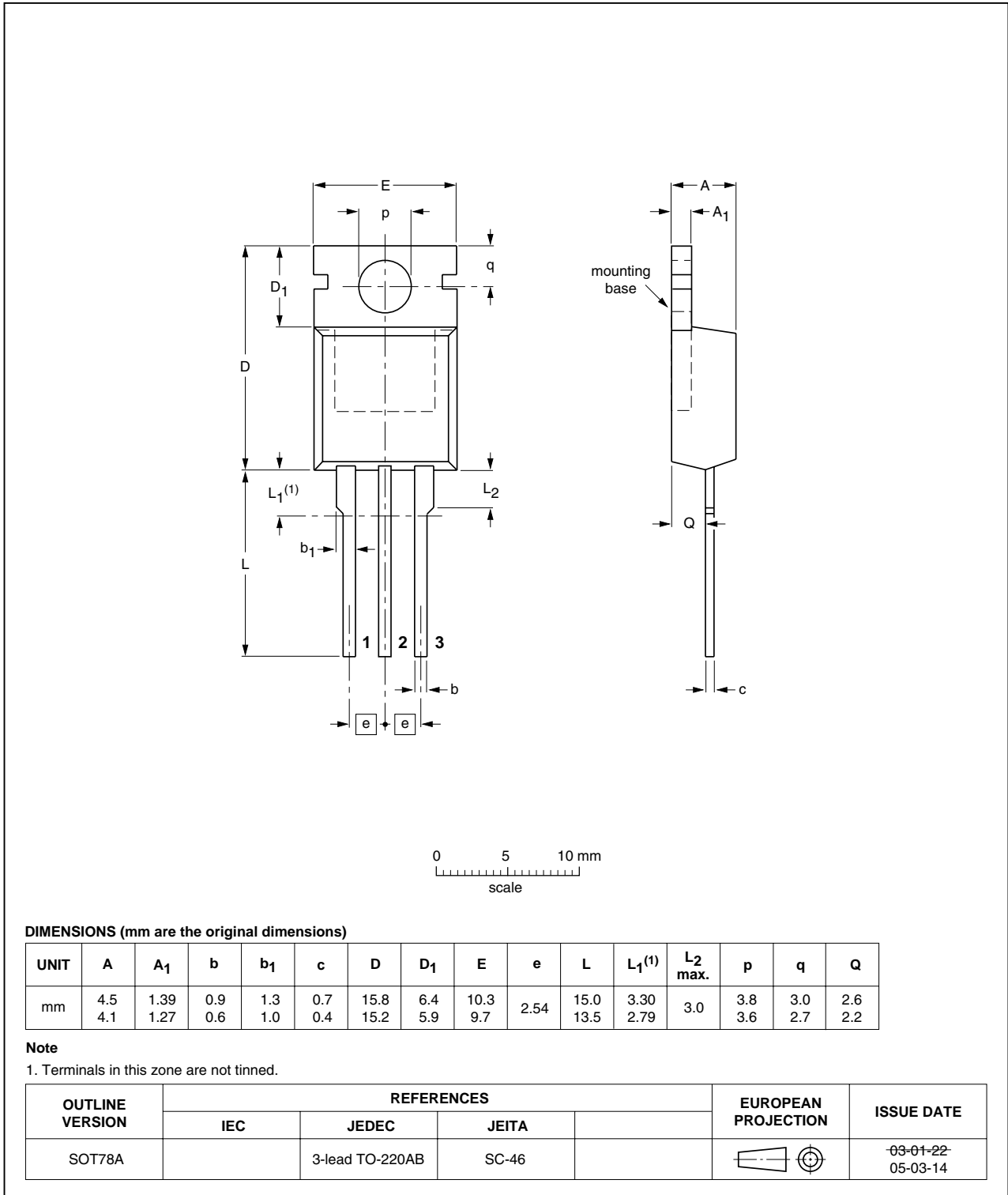


Fig 17. Package outline SOT78A (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK753R4-30B v.2	20110421	Product data sheet	-	BUK75_763R4-30B_1
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Type number BUK753R4-30B separated from data sheet BUK75_763R4-30B_1.</li></ul>			
BUK75_763R4-30B_1	20060105	Product specification	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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